Quad 2-input NAND gate Rev. 1 — 12 July 2012

Product data sheet

1. **General description**

The 74HC00-Q100; 74HCT00-Q100 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC00-Q100; 74HCT00-Q100 provides a quad 2-input NAND function.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1) Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Input levels:
 - For 74HC00-Q100: CMOS level
 - For 74HCT00-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Multiple package options

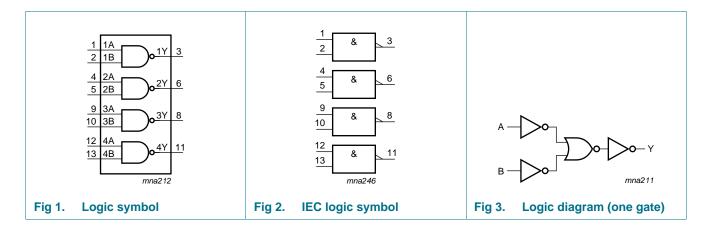


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3. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74HC00D-Q100	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1					
74HCT00D-Q100			3.9 mm						
74HC00PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1					
74HCT00PW-Q100			body width 4.4 mm						
74HC00BQ-Q100	–40 °C to +125 °C	DHVQFN14	F	SOT762-1					
74HCT00BQ-Q100			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm						

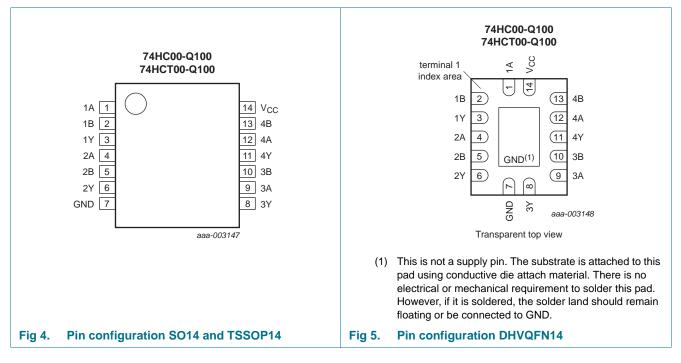
4. Functional diagram



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5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1] Input Output nA nΒ nY Х L Н Х L н Н Н L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2] _	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 package: Ptot derates linearly with 8 mW/K above 70 °C.

For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C. For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC	74HC00-Q100			74HCT00-Q100		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

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9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	to +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC00-	-Q100									
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	-	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	-	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	-	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	-	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	-	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	-	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
output voltag	output voltage	I_{O} = –20 $\mu\text{A};$ V_{CC} = 2.0 V	-	2.0	-	1.9	-	1.9	-	V
		I_O = –20 $\mu A;~V_{CC}$ = 4.5 V	-	4.5	-	4.4	-	4.4	-	V
		I_{O} = –20 $\mu A;~V_{CC}$ = 6.0 V	-	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	-	4.32	-	3.84	-	3.7	-	V
		I_{O} = –5.2 mA; V_{CC} = 6.0 V	-	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_O = 20 $\mu A; V_{CC}$ = 2.0 V	-	0	-	-	0.1	-	0.1	V
		I_O = 20 $\mu A;V_{CC}$ = 4.5 V	-	0	-	-	0.1	-	0.1	V
		I_O = 20 $\mu A; V_{CC}$ = 6.0 V	-	0	-	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	-	-	0.33	-	0.4	V
		I_{O} = 5.2 mA; V_{CC} = 6.0 V	-	0.16	-	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	-	-	±1	-	±1	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	-	-	20	-	40	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

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Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	-40 °C t	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HCT0	0-Q100									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	-	-	0.8	-	0.8	V
V _{OH} HIGH-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$									
	output voltage	I _O = -20 μA	-	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	-	4.32	-	3.84	-	3.7	-	V
OL -	LOW-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$								
	output voltage	$I_O = 20 \ \mu\text{A}; V_{CC} = 4.5 \ \text{V}$	-	0	-	-	0.1	-	0.1	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.15	-	-	0.33	-	0.4	V
I	input leakage current	$V_1 = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	-	-	±1	-	±1	μA
I _{CC}	supply current		-	-	-	-	20	-	40	μA
∆l _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	150	-	-	675	-	735	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 V; C_L = 50 pF;$ for load circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions			25 °C		–40 °C to	o +125 ℃	Unit
			-	Min	Тур	Мах	Max (85 °C)	Max (125 °C)	
74HC00-	Q100								
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[1]						
	$V_{CC} = 2.0 V$		-	25	-	115	135	ns	
		$V_{CC} = 4.5 V$		-	9	-	23	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 V$		-	7	-	20	23	ns
tt	transition time	see Figure 6	[2]						
		$V_{CC} = 2.0 V$		-	19	-	95	110	ns
		$V_{CC} = 4.5 V$		-	7	-	19	22	ns
		$V_{CC} = 6.0 V$		-	6	-	16	19	ns
C _{PD}	power dissipation capacitance	per package; $V_1 = GND$ to V_{CC}	<u>[3]</u>	-	22	-	-	-	pF

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Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		Unit
			-	Min	Тур	Max	Max (85 °C)	Max (125 °C))
74HCT00)-Q100	'							
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	12	-	24	29	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[2]	-	-	-	29	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	22	-	-	-	pF

Dynamic characteristics ... continued Table 7. GND = 0 V: $C_1 = 50$ pE: for load circuit see Figure 7.

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

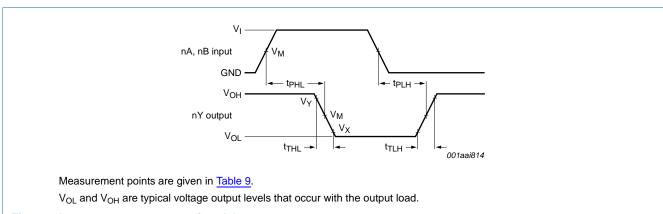
 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Input to output propagation delays Fig 6.

Table 8. **Measurement points**

Туре	Input	Output				
	V _M	V _M	V _X	V _Y		
74HC00-Q100	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}		
74HCT00-Q100	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}		

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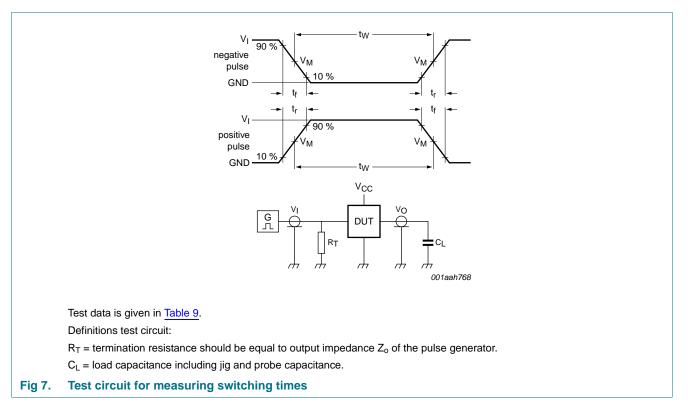


Table 9. Test data

Туре	Input L		Load	Test
	VI	t _r , t _f	CL	
74HC00-Q100	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT00-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

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12. Package outline

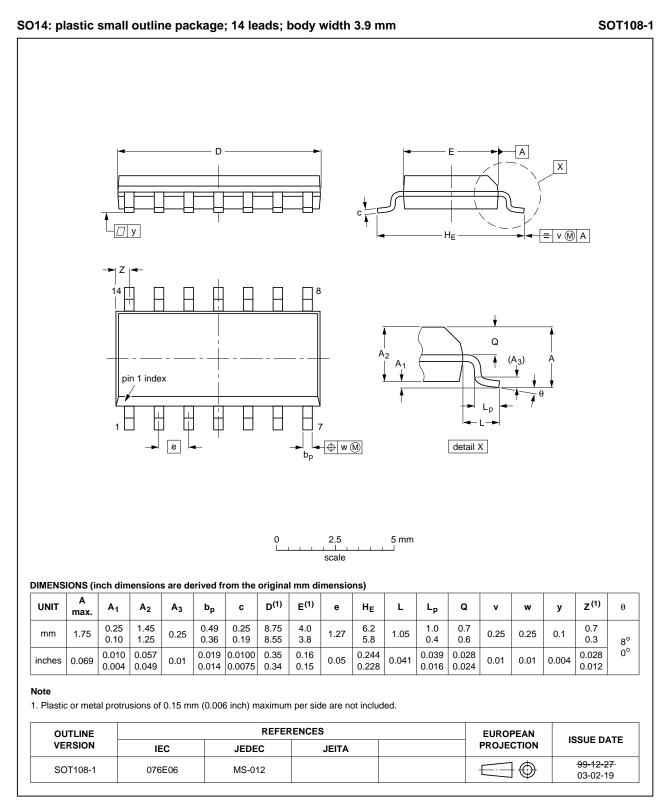


Fig 8. Package outline SOT108-1 (SO14)

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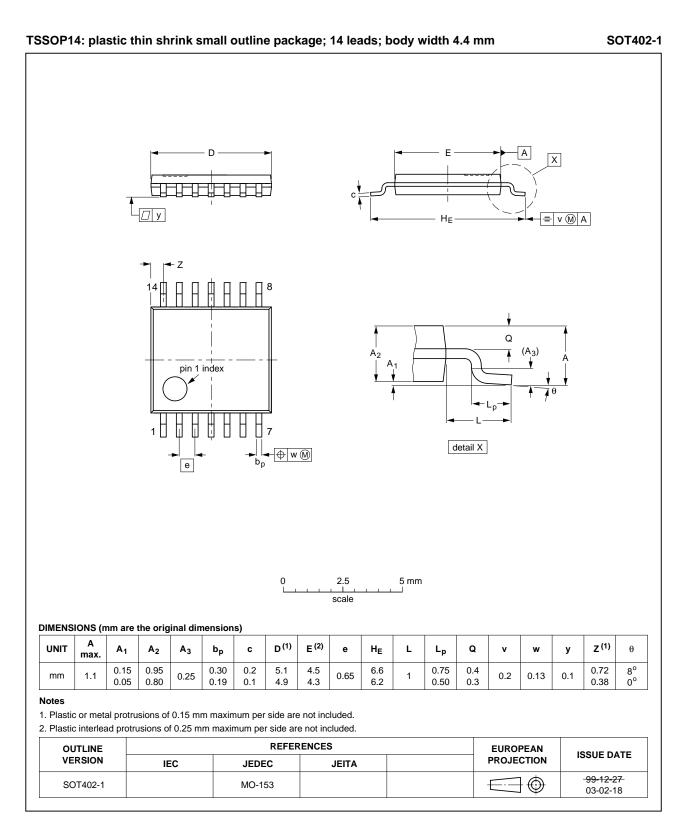
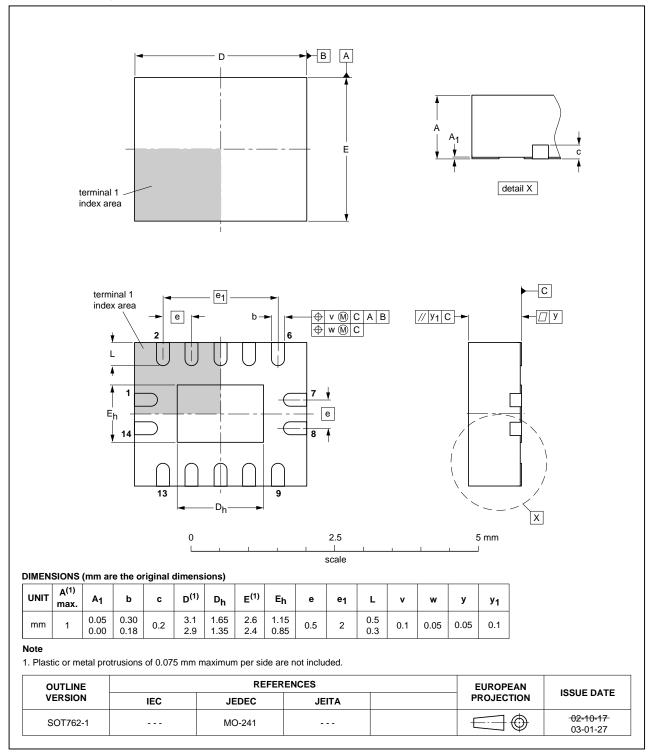


Fig 9. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 10. Package outline SOT762-1 (DHVQFN14)

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13. Abbreviations

AcronymDescriptionCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMMMachine ModelTTLTransistor-Transistor LogicMILMilitary	Table 10.	Abbreviations
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMMMachine ModelTTLTransistor-Transistor Logic	Acronym	Description
ESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMMMachine ModelTTLTransistor-Transistor Logic	CMOS	Complementary Metal-Oxide Semiconductor
HBM Human Body Model LSTTL Low-power Schottky Transistor-Transistor Logic MM Machine Model TTL Transistor-Transistor Logic	DUT	Device Under Test
LSTTLLow-power Schottky Transistor-Transistor LogicMMMachine ModelTTLTransistor-Transistor Logic	ESD	ElectroStatic Discharge
MM Machine Model TTL Transistor-Transistor Logic	HBM	Human Body Model
TTL Transistor-Transistor Logic	LSTTL	Low-power Schottky Transistor-Transistor Logic
	MM	Machine Model
MIL Military	TTL	Transistor-Transistor Logic
•	MIL	Military

14. Revision history

Table 11. Revision history									
Document ID	Release date	Data sheet status	Change notice	Supersedes					
74HC_HCT00_Q100 v.1	20120712	Product data sheet	-	-					

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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